



2N4401

NPN GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 40 Volts **POWER** 625 mWatts

FEATURES

- NPN epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = 40V$
- Collector current $I_C = 600mA$
- Complimentary (PNP) device: 2N4403
- Pb free product are available :99% Sn above can meet RoHS environment substance directive request

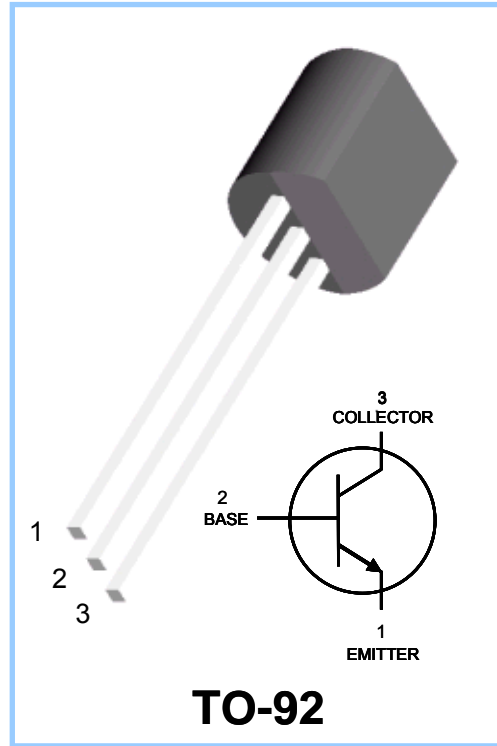
MECHANICAL DATA

Case: TO-92

Terminals: Solderable per MIL-STD-202, Method 208

Approx Weight : 0.02grams

Marking : 4401



ABSOLUTE MAXIMUM RATINGS

PARAMETER	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	40	V
Collector - Base Voltage	V_{CBO}	60	V
Emitter - Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	600	mA

THERMAL CHARACTERISTICS

PARAMETER	Symbol	Value	Units
Max Power Dissipation	P_{TOT}	625	mW
Storage Temperature	T_{STG}	-55 to 150	°C
Junction Temperature	T_J	-55 to 150	°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W



2N4401

ELECTRICAL CHARACTERISTICS ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1.0\text{mA}$, $I_E=0$	40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	60	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	6.0	-	-	V
Base Cutoff Current	I_{BEV}	$V_{CE}=35\text{V}$, $V_{EB}=0.4\text{V}$	-	-	100	nA
Collector Cutoff Current	I_{CEX}	$V_{CE}=35\text{V}$, $V_{EB}=0.4\text{V}$	-	-	100	nA
DC Current Gain	h_{FE}	$I_C=0.1\text{mA}$, $V_{CE}=1.0\text{V}$	20	-	-	-
		$I_C=1.0\text{mA}$, $V_{CE}=1.0\text{V}$	40	-	-	
		$I_C=10\text{mA}$, $V_{CE}=1.0\text{V}$	80	-	-	
		$I_C=150\text{mA}$, $V_{CE}=1.0\text{V}$	100	-	300	
		$I_C=500\text{mA}$, $V_{CE}=2.0\text{V}$	40	-	-	
Collector - Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=150\text{mA}$, $I_B=15\text{mA}$ $I_C=500\text{mA}$, $I_B=50\text{mA}$	-	-	0.4 0.75	V
Base - Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C=150\text{mA}$, $I_B=15\text{mA}$ $I_C=500\text{mA}$, $I_B=50\text{mA}$	0.75 -	-	0.95 1.2	V
Current-Gain - Bandwidth Product	f_T	$I_C=200\text{mA}$, $V_{CE}=10\text{V}$ $f=100\text{MHz}$	250	-	-	MHz
Collector-Base Capacitance	C_{CBO}	$V_{CB}=5.0\text{V}$, $I_E=0$, $f=1\text{MHz}$	-	-	6.5	pF
Emitter - Base Capacitance	C_{EBO}	$V_{CB}=5.0\text{V}$, $I_E=0$, $f=1\text{MHz}$	-	-	30	pF
Delay Time	t_d	$V_{CC}=30\text{V}$, $V_{BE}=2.0\text{V}$, $I_C=150\text{mA}$, $I_{B1}=15\text{mA}$	-	-	15	ns
Rise Time	t_r		-	-	20	ns
Storage Time	t_s		-	-	225	ns
Fall Time	t_f	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$ $I_{B1}=I_{B2}=15\text{mA}$	-	-	30	ns

SWITCHING TIME EQUIVALENT TEST CIRCUITS

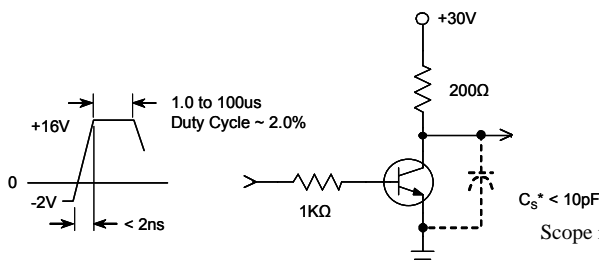


Fig. 1. Turn-On Time

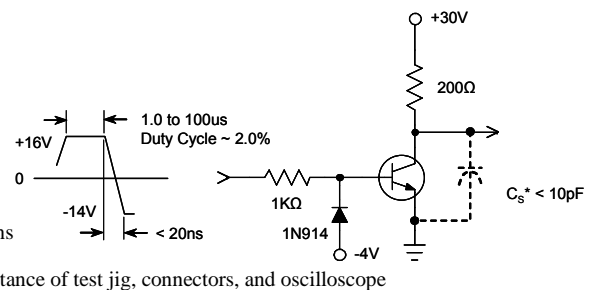


Fig. 2. Turn-Off Time

* Total shunt capacitance of test jig, connectors, and oscilloscope



ELECTRICAL CHARACTERISTICS CURVE

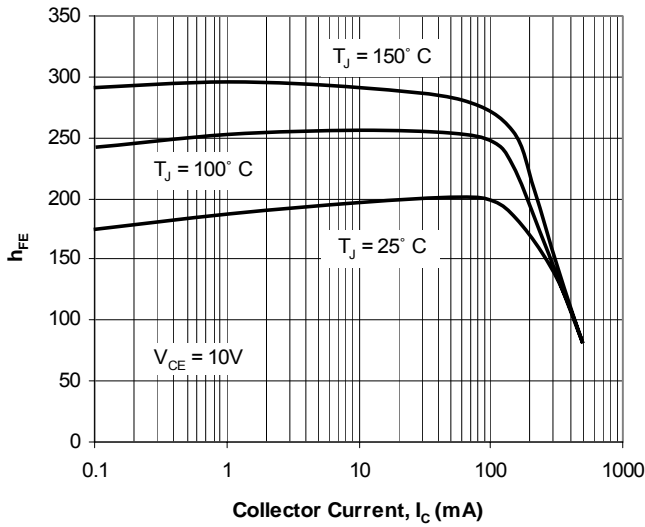


Fig. 3. Typical h_{FE} vs Collector Current

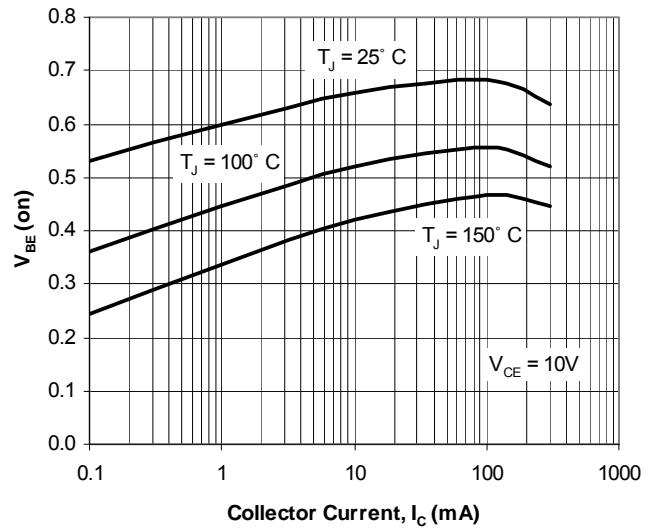


Fig. 4. Typical V_{BE} vs Collector Current

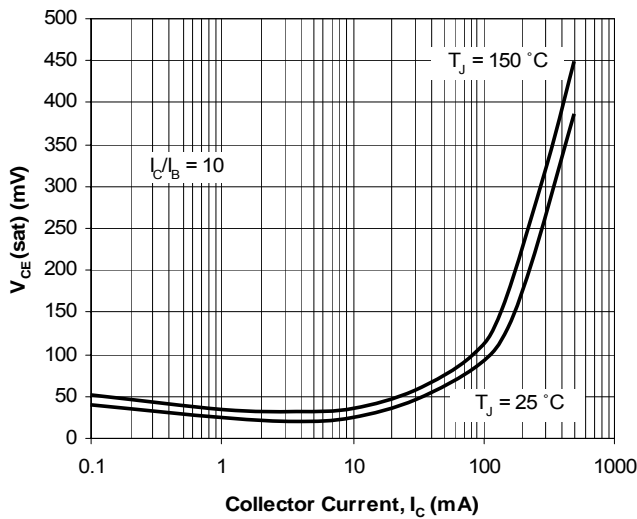


Fig. 5. Typical $V_{CE(sat)}$ vs Collector Current

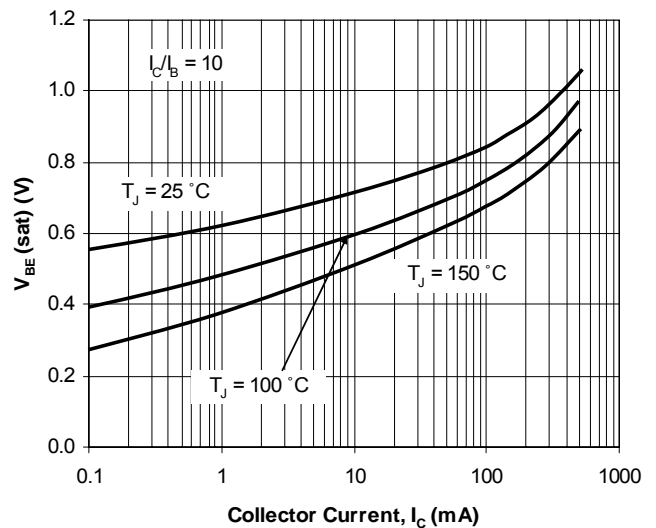


Fig. 6. Typical $V_{BE(sat)}$ vs Collector Current

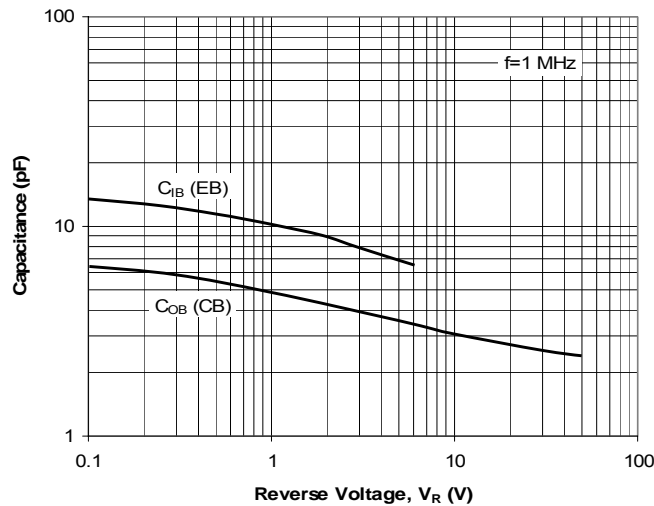


Fig. 7. Typical Capacitances vs Reverse Voltage

2N4401

TO-92 Case Outline

